

2SB0956G

Silicon PNP epitaxial planar type

For low-frequency output amplification

Complementary to 2SD1280G

■ Features

- Large collector power dissipation P_C
- Low collector-emitter saturation voltage $V_{CE(sat)}$
- Mini Power type package, allowing downsizing of the equipment and automatic insertion through the tape packing and the magazine packing.

■ Package

- Code
MiniP3-F2
- Pin Name
1: Base
2: Collector
3: Emitter

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	V_{CBO}	-20	V
Collector-emitter voltage (Base open)	V_{CEO}	-20	V
Emitter-base voltage (Collector open)	V_{EBO}	-5	V
Collector current	I_C	-1	A
Peak collector current	I_{CP}	-2	A
Collector power dissipation *	P_C	1	W
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

■ Marking Symbol: H

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Note) *: Print circuit board: Copper foil area of 1 cm² or more, and the board thickness of 1.7 mm for the collector portion

■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

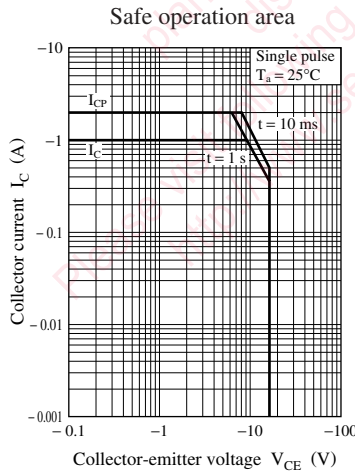
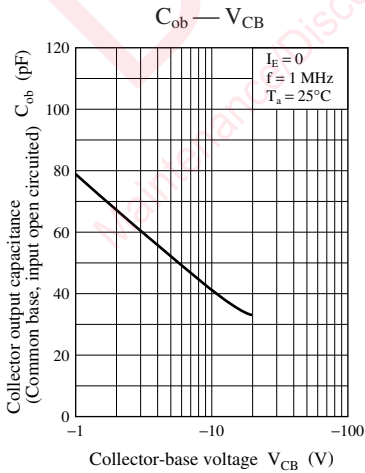
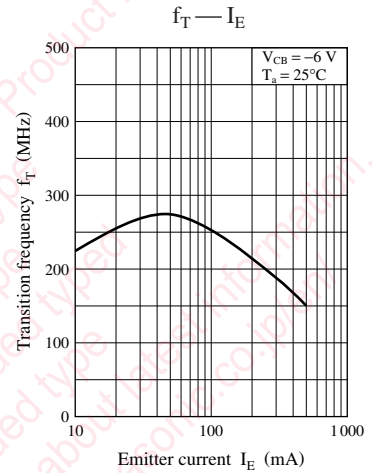
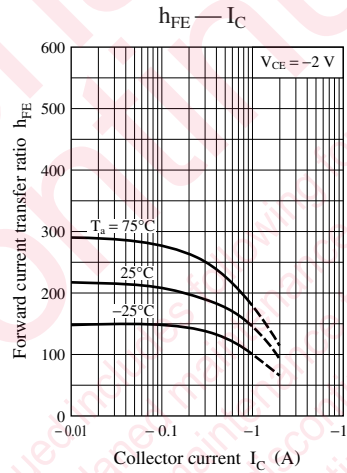
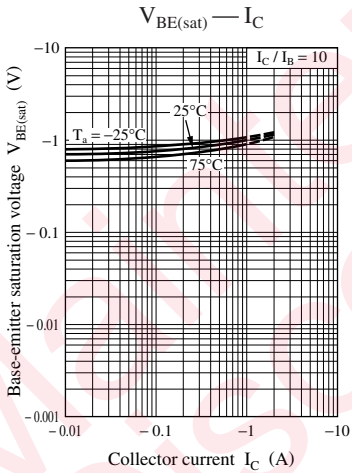
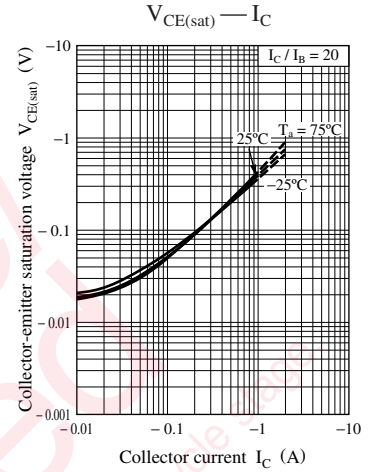
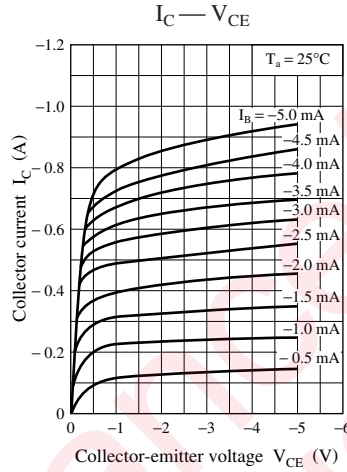
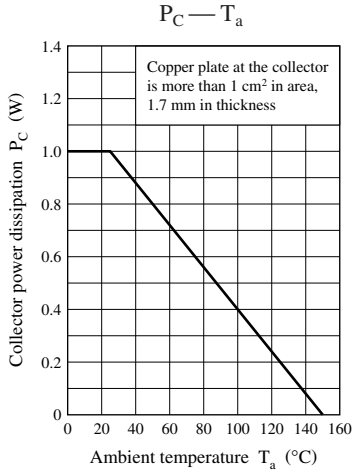
Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-emitter voltage (Base open)	V_{CEO}	$I_C = -1 \text{ mA}, I_B = 0$	-20			V
Emitter-base voltage (Collector open)	V_{EBO}	$I_E = -10 \mu\text{A}, I_C = 0$	-5			V
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{CB} = -10 \text{ V}, I_E = 0$			-1	μA
Forward current transfer ratio *1	h_{FE1} *2	$V_{CE} = -2 \text{ V}, I_C = -500 \text{ mA}$	130		280	—
	h_{FE2}	$V_{CE} = -2 \text{ V}, I_C = -1.5 \text{ A}$	50			
Collector-emitter saturation voltage *1	$V_{CE(sat)}$	$I_C = -1 \text{ A}, I_B = -50 \text{ mA}$			-0.5	V
Base-emitter saturation voltage *1	$V_{BE(sat)}$	$I_C = -500 \text{ mA}, I_B = -50 \text{ mA}$			-1.2	V
Transition frequency	f_T	$V_{CB} = -6 \text{ V}, I_E = 50 \text{ mA}, f = 200 \text{ MHz}$		200		MHz
Collector output capacitance (Common base, input open circuited)	C_{ob}	$V_{CB} = -6 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		40		pF

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

2. *1: Pulse measurement

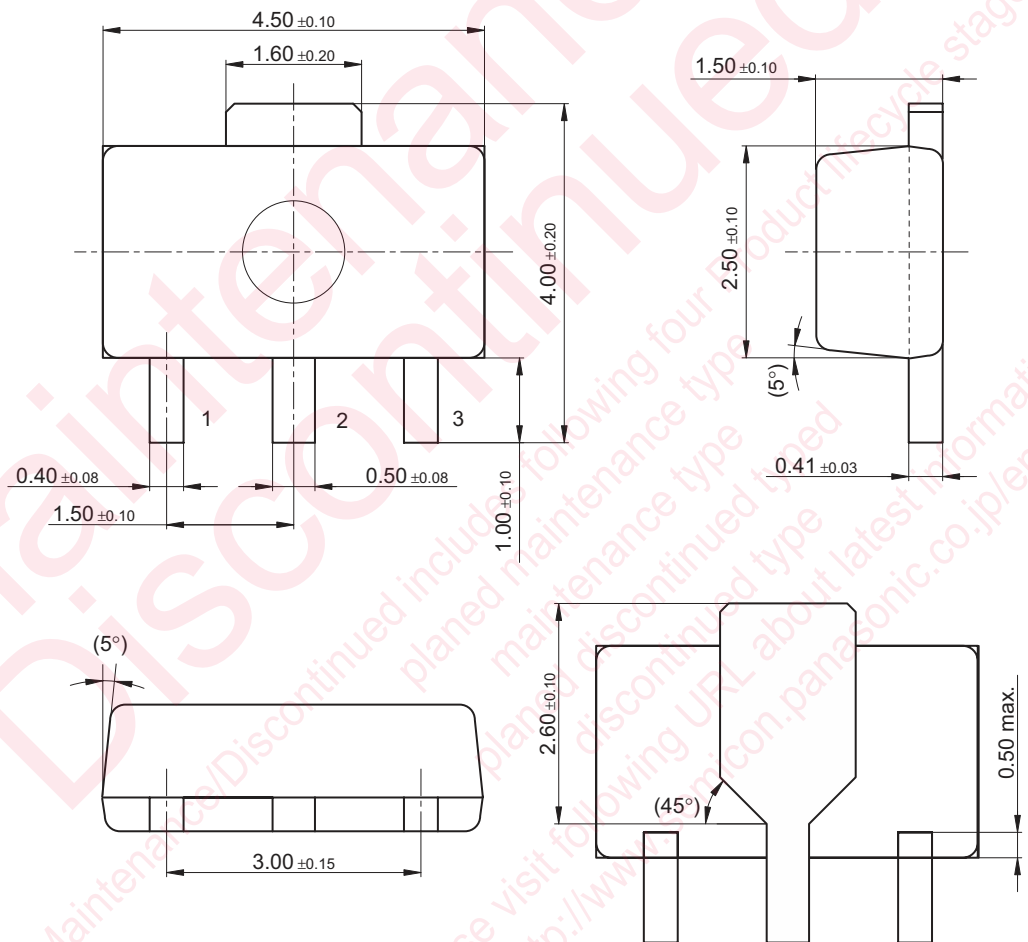
*2: Rank classification

Rank	R	S
h_{FE1}	130 to 210	180 to 280



MiniP3-F2

Unit: mm



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